# NGTD13T120F2

# **IGBT** Die

Trench Field Stop II IGBT Die for motor drive and inverter applications.

### Features

- Extremely Efficient Trench with Field Stop Technology
- Low V<sub>CE(sat)</sub> Loss Reduces System Power Dissipation

### **Typical Applications**

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^{\circ}C$	V <sub>CE</sub>	1200	V
DC Collector Current, limited by $T_{J(\text{max})}$	۱ <sub>C</sub>	(Note 1)	A
Pulsed Collector Current (Note 2)	I <sub>C, pulse</sub>	60	А
Gate-Emitter Voltage	V <sub>GE</sub>	±20	V
Maximum Junction Temperature	ТJ	-55 to +175	°C
Short Circuit Withstand Time, $V_{GE}$ = 15 V, $V_{CE}$ = 500V, $T_J$ $\leq$ 150°C	T <sub>SC</sub>	10	μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly. 2.  $T_{pulse}$  limited by  $T_{jmax}$ , 10 µs pulse,  $V_{GE}$  = 15 V.

### **MECHANICAL DATA**

Parameter	Value	Unit	
Die Size	3476 x 3580	μm <sup>2</sup>	
Emitter Pad Size	See die layout µm <sup>2</sup>		
Gate Pad Size	405 x 670 μm <sup>2</sup>		
Die Thickness	5	mils	
Wafer Size	150	mm	
Top Metal	5 μm AlSi		
Back Metal	2 μm TiNiAg		
Max possible chips per wafer	766		
Passivation frontside	Oxide-Nitride		
Reject ink dot size	25 mils		
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Bare Wafer in Jar Storage time: < 36 months	Type: Die on tape in ring–pack Storage time: < 3 months	

### **ORDERING INFORMATION**

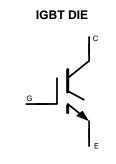
Device	Inking?	Shipping	
NGTD13T120F2WP	Yes	Bare Wafer in Jar	
NGTD13T120F2SWK	Yes	Sawn Wafer on Tape	



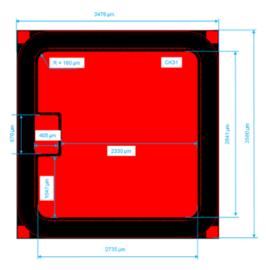
## **ON Semiconductor®**

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 $V_{RCE} = 1200 V$  $I_{C}$  = Limited by  $T_{J(max)}$ 



**DIE OUTLINE** 



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### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ , unless otherwise specified)

**Output Capacitance** 

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units
STATIC CHARACTERISTICS				•		
Collector-Emitter Breakdown Voltage	$V_{GE}$ = 0 V, I <sub>C</sub> = 500 µA	V <sub>(BR)CES</sub>	1200			V
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 15 A	V <sub>CE(sat)</sub>		2.0	2.4	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400 \ \mu A$	V <sub>GE(TH)</sub>	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1200 V	I <sub>CES</sub>			1.0	mA
Gate Leakage Current	$V_{GE} = 20 \text{ V}, \text{ V}_{CE} = 0 \text{ V}$	I <sub>GES</sub>			200	mA
DYNAMIC CHARACTERISTICS						
Input Capacitance		Cies		2640		pF

 $V_{CE} = 20 \text{ V}, V_{GE} = 0 \text{ V}, f = 1$ MHz Reverse Transfer Capacitance Cres 50 pF Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

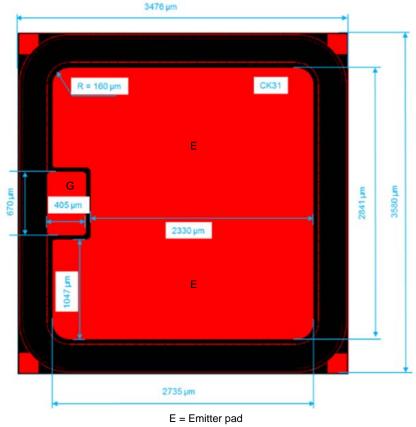
Coes

pF

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performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **DIE LAYOUT**



G = Gate pad All dimensions in µm

### NGTD13T120F2

### **Further Electrical Characteristic**

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

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